Ordering number : EN6555B

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

5LN01C — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Ultrahigh-speed switching
- 2.5V drive

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		50	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		0.1	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	0.4	A
Allowable Power Dissipation	P_D		0.25	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C

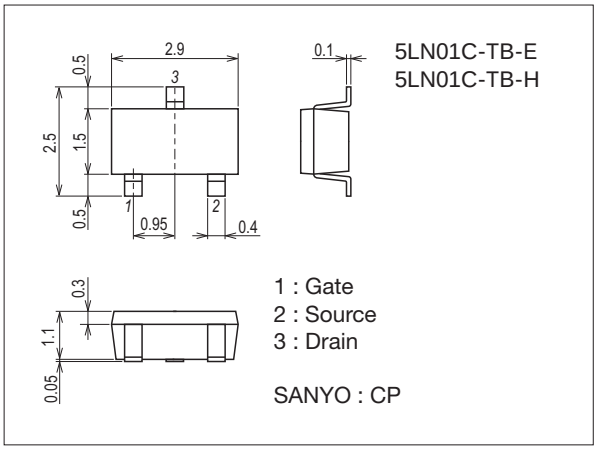
This product is designed to "ESD immunity < 200V*", so please take care when handling.

* Machine Model

Package Dimensions

unit : mm (typ)

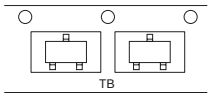
7013A-013



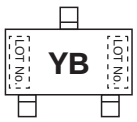
Product & Package Information

- Package : CP
- JEITA, JEDEC : SC-59, TO-236, SOT-23, TO-236AB
- Minimum Packing Quantity : 3,000 pcs./reel

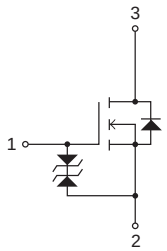
Packing Type: TB



Marking



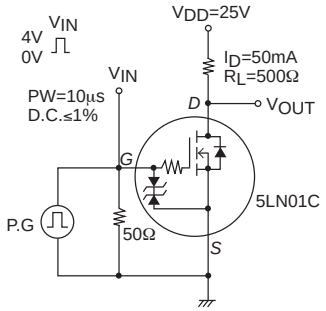
Electrical Connection



Electrical Characteristics at Ta=25°C

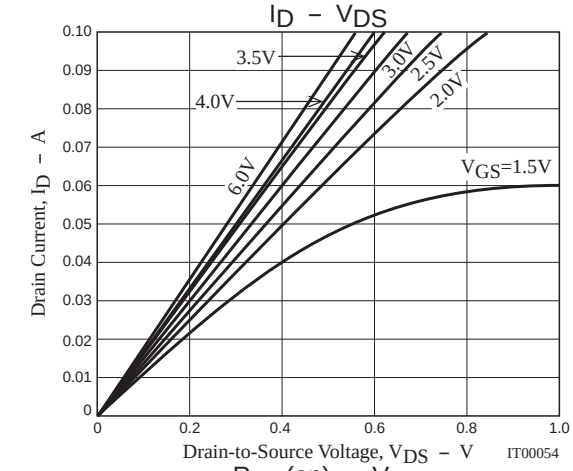
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	50			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=50V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0V			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=100μA	0.4		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=50mA	0.13	0.18		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=50mA, V_{GS}=4V		6	7.8	Ω
	R_{DS}(on)2	I_D=30mA, V_{GS}=2.5V		7.1	9.9	Ω
	R_{DS}(on)3	I_D=10mA, V_{GS}=1.5V		10	20	Ω
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		6.6		pF
Output Capacitance	Coss			4.7		pF
Reverse Transfer Capacitance	Crss			1.7		pF
Turn-ON Delay Time	t_d(on)	See specified Test Circuit.		18		ns
Rise Time	t_r			42		ns
Turn-OFF Delay Time	t_d(off)			190		ns
Fall Time	t_f			105		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=100mA		1.57		nC
Gate-to-Source Charge	Qgs			0.20		nC
Gate-to-Drain “Miller” Charge	Qgd			0.32		nC
Diode Forward Voltage	V_{SD}	I_S=100mA, V_{GS}=0V		0.85	1.2	V

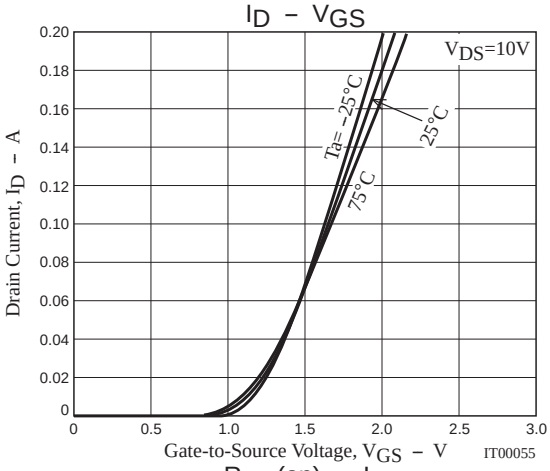
Switching Time Test Circuit

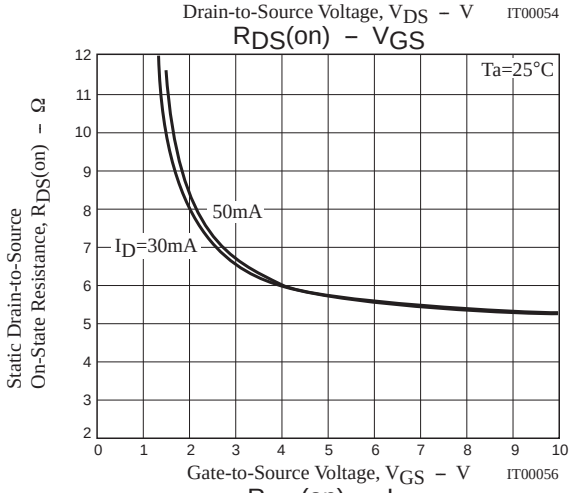


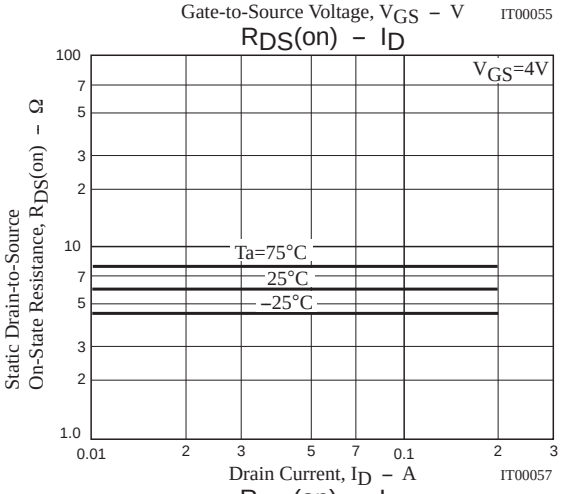
Ordering Information

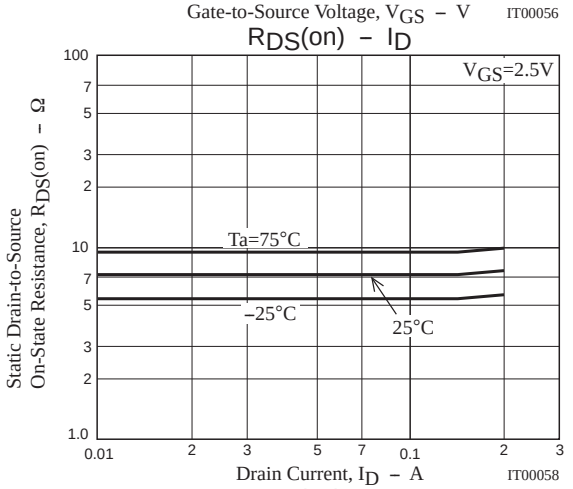
Device	Package	Shipping	memo
5LN01C-TB-E	CP	3,000pcs./reel	Pb Free
5LN01C-TB-H	CP	3,000pcs./reel	Pb Free and Halogen Free

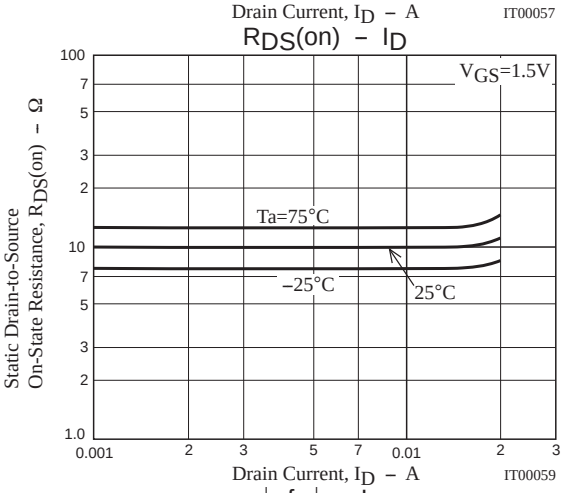


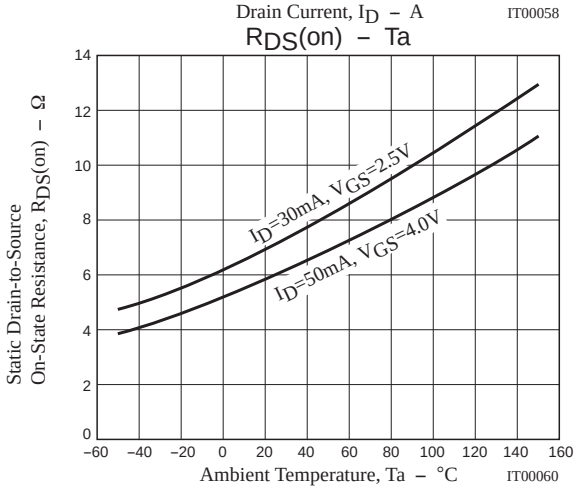


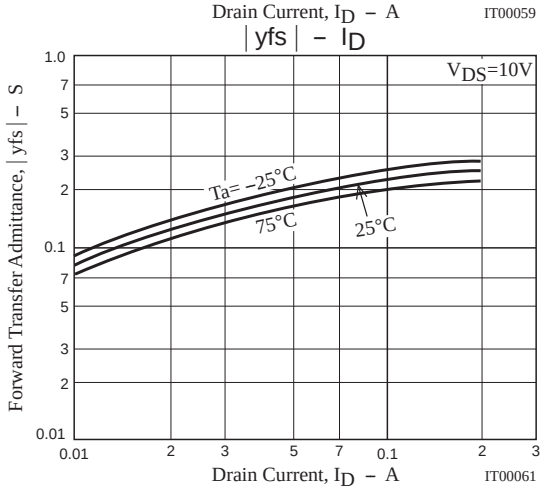


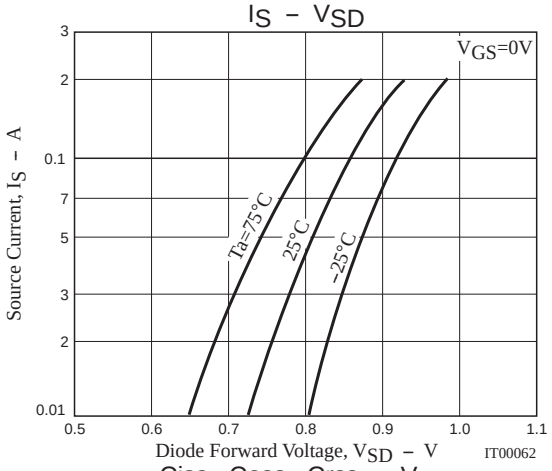


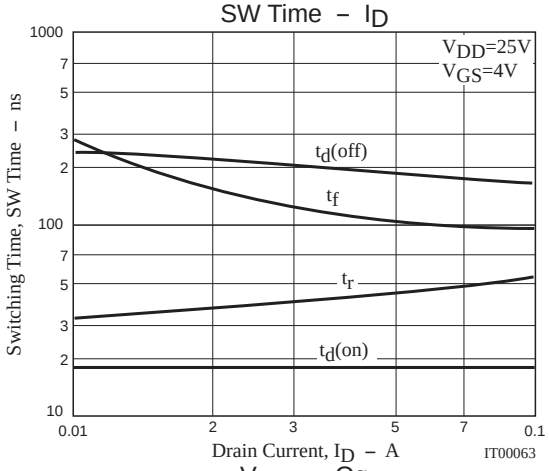


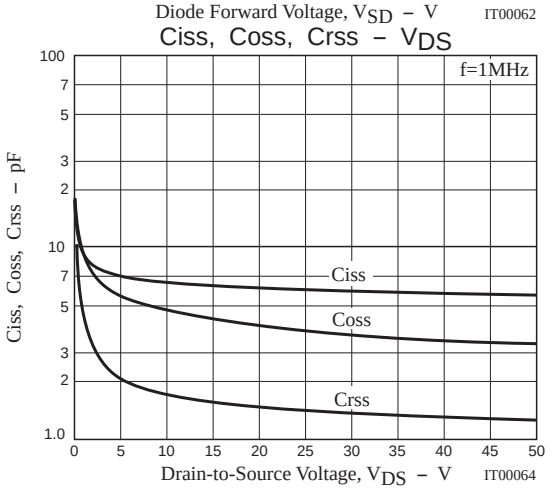


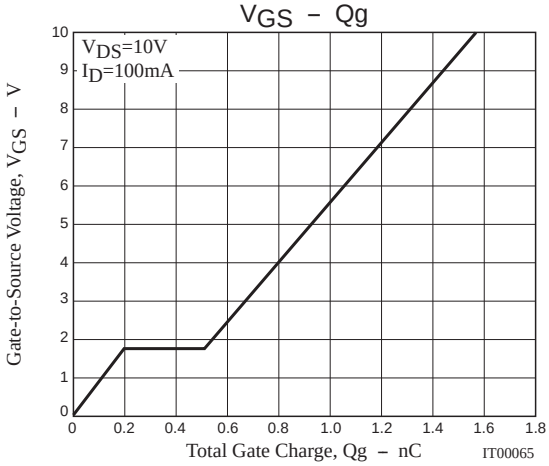


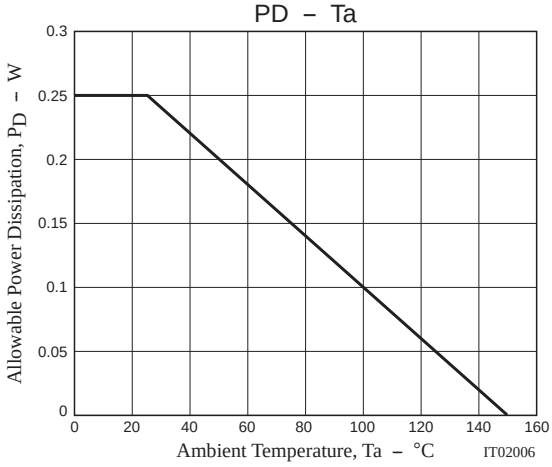












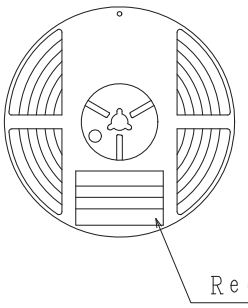
Embossed Taping Specification

5LN01C-TB-E, 5LN01C-TB-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
CP	CP	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

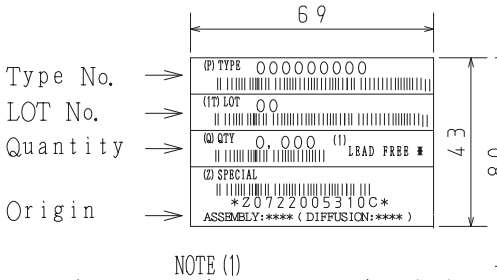
Packing method



Reel label

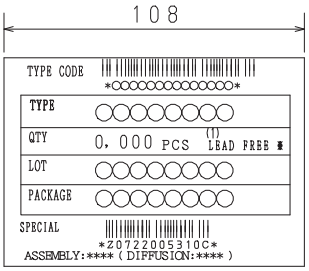
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



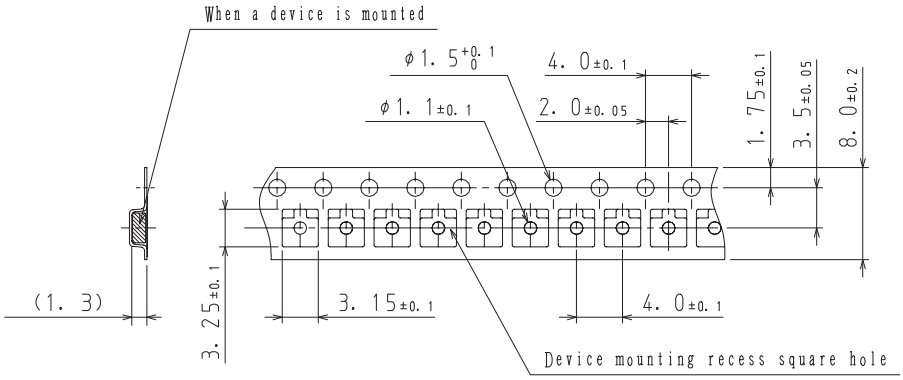
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

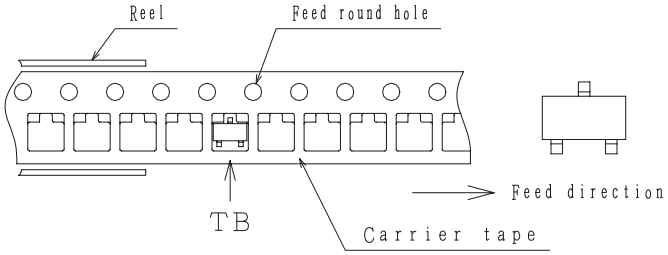
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



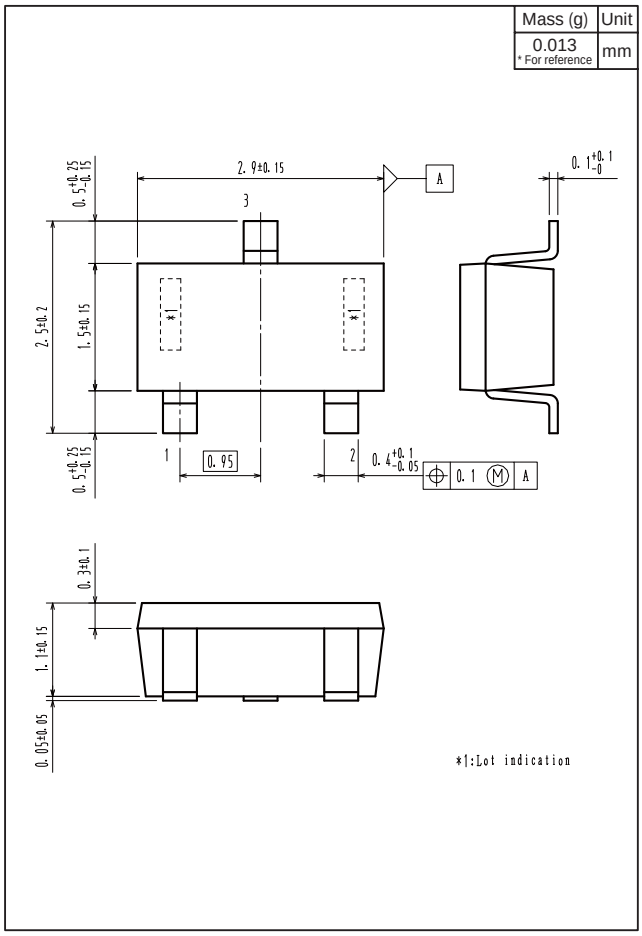
2-2. Device placement direction



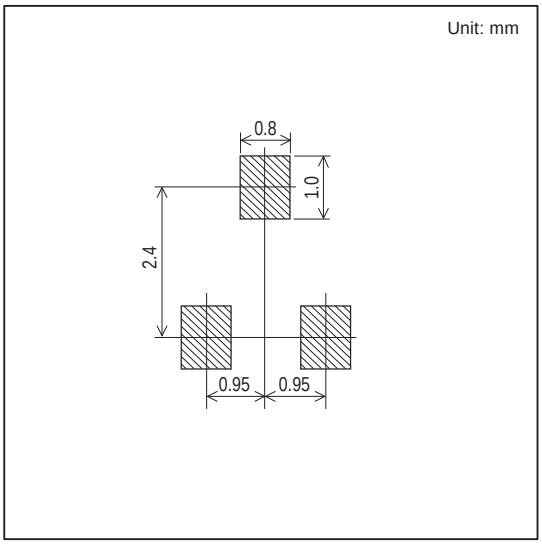
Those with one electrode terminal on the feed hole side·····TB

Outline Drawing

5LN01C-TB-E, 5LN01C-TB-H



Land Pattern Example



Note on usage : Since the 5LN01C is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.